

GaAs MMIC Absorptive SPDT Switch Chip, DC- 8 GHz

Performance characteristics

- Frequency range: DC 8 GHz
- Insertion loss : 1.1 dB
- Isolation: 45 dB
- On-state VSWR : 1.2
- 500hm input/output
- QFN4X4mm

Product Introduction

GSW-0008DT is a GaAs MMIC absorptive single-pole double-throw switch chip with 50Ω matching at the input/output ends, a frequency range covering DC ~ 8 GHz, and 0V/-5V power supply. The switching speed is 10ns. The amplifier adopts a 4X4mm surface-mount leadless ceramic tube shell to achieve airtight packaging. The surface of the pin pad is gold-plated and is suitable for reflow soldering installation.

Use restriction parameter ¹		
Control voltage range	-8V \sim +0.5V	
Maximum input power	+30dBm	
Operating temperature	-55 ~ +85°C	
Storage temperature	-65 ~ +150°C	

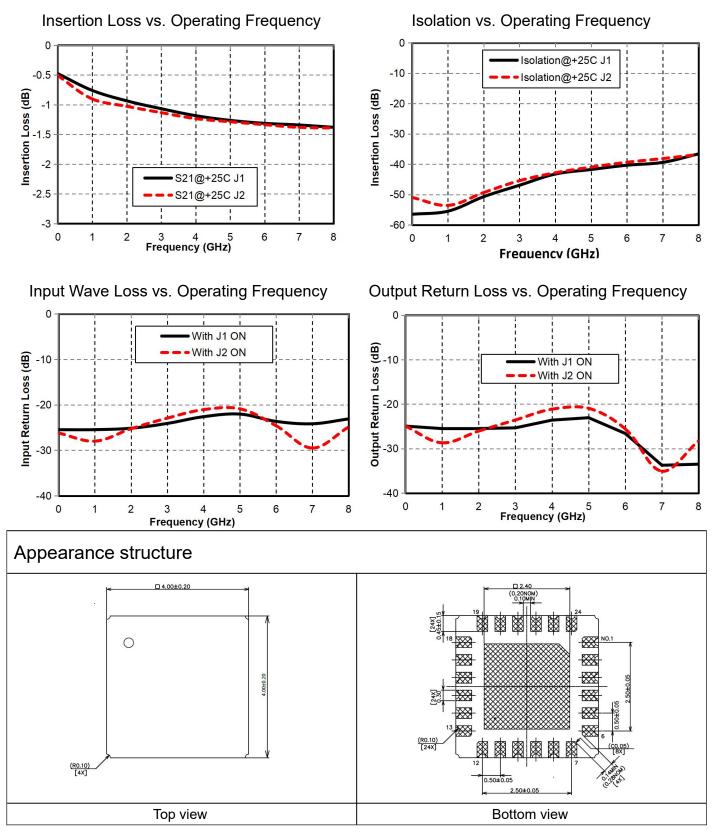
[1] Exceeding any of these maximum limits may cause permanent damage.

Electrical Parameters (TA = +25°C)					
Index	Minimum	Typical Value	Maximum	Unit	
Frequency Range		DC-8		G Hz	
Insertion loss	-	1.1	1.4	dB	
Isolation	36	45	-	dB	
Input return loss	22	23	-	dB	
Output return loss	20	23	-	dB	
P-1dB	-	23	-	dBm	
Switching speed	-	10	-	ns	



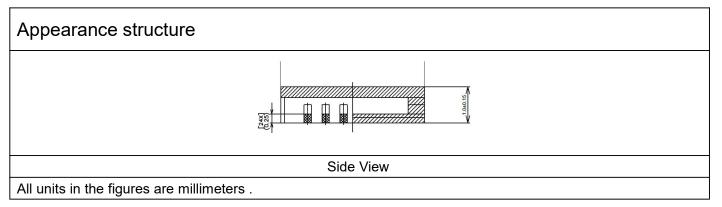
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Main index test curve





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Truth table :

V SE	V S	IN-OUT1	IN-OUT2
-5V	0V	Conductivity	closure
0V	-5V	closure	Conductivity

Pin Definition

Pin number	Function Symbol	Functional Description
3	RFIN	The signal input terminal is connected to a 50 ohm circuit, and there is
		no DC blocking capacitor integrated into the chip.
9, 22	RF OUT1/2	The signal output terminal is connected to a 50 ohm circuit, and there
		is no DC blocking capacitor integrated into the chip.
2, 4, 8, 10, 21, 23	GND	The bottom of the chip needs to be well grounded to RF and DC
14, 17	Voltage Control	For on/off control, VSE and VSH can use any one of the two groups.
other	NC	The pin is left floating and can be grounded

Application Circuit

